

N-channel 40V - 0.0035Ω - 120A - D²PAK - TO-220
planar STripFET™ Power MOSFET

Features

Type	V _{DSS}	R _{DS(on)} Max	I _D	P _w
STB200N4F3	40V	<0.0040Ω	120A	300W
STP200N4F3	40V	<0.0044Ω	120A	300W

- 100% avalanche tested
- Standard threshold drive

Applications

- Switching applications
 - Automotive

Description

This Power MOSFET is the latest development of STMicroelectronics unique “single feature size™” strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility. this new improved device has been specifically designed for automotive applications.

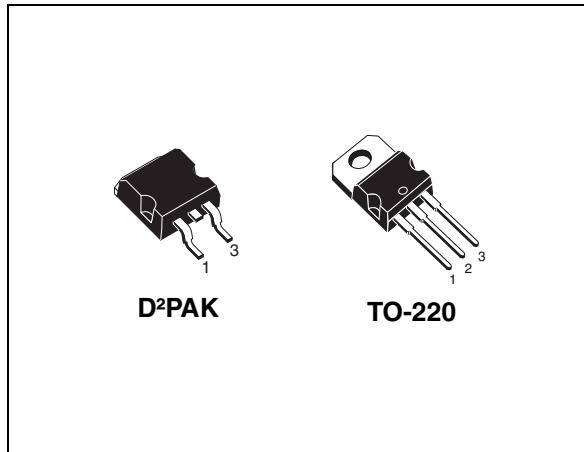


Figure 1. Internal schematic diagram

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB200N4F3	200N4F3	D ² PAK	Tape & reel
STP200N4F3	200N4F3	TO-220	Tube

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1 Electrical ratings

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Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	40	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	120	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	120	A
$I_{DM}^{(2)}$	Drain current (pulsed)	480	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	300	W
	Derating factor	2.0	W/ $^\circ\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy	862	mJ
$dv/dt^{(4)}$	Peak diode recovery voltage slope	4.2	V/ns
T_j T_{stg}	Operating junction temperature Storage temperature	-55 to 175	$^\circ\text{C}$

1. Current limited by package
2. Pulse width limited by safe operating area
3. Starting $T_j = 25^\circ\text{C}$, $I_D = 60\text{A}$, $V_{DD} = 25\text{V}$
4. $I_{SD} \leq 60\text{A}$, $di/dt \leq 440 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$.

Table 3. Thermal data

Symbol	Parameter	Value		Unit
		TO-220	D ² PAK	
R _{thj-case}	Thermal resistance junction-case max	0.50		$^\circ\text{C}/\text{W}$
R _{thj-pcb} ⁽¹⁾	Thermal resistance junction-pcb max	--	35	$^\circ\text{C}/\text{W}$
R _{thj-amb}	Thermal resistance junction-ambient max	62.5	--	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board, 1inch² 2 oz. Cu.

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

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Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu\text{A}, V_{GS} = 0$	40			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}, V_{DS} = \text{Max rating } @ 125^{\circ}\text{C}$			10 100	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{V}$			± 100	nA
$V_{GS(\text{th})}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2		4	V
$R_{DS(\text{on})}$	Static drain-source on resistance	$V_{GS} = 10\text{V}, I_D = 80\text{A}$ D²PAK TO-220		0.0035 0.0040	0.0040 0.0044	Ω Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 10\text{V}, I_D = 80\text{A}$		200		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{V}, f = 1 \text{ MHz}, V_{GS} = 0$		5100 1270 37		pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 20\text{V}, I_D = 120\text{A}$ $V_{GS} = 10\text{V}$ (see Figure 14)		75 23 17		nC nC nC

1. Pulsed: pulse duration=300μs, duty cycle 1.5%

Table 6. Switching times

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
$t_{d(on)}$ t_r	Turn-on delay time	$V_{DD}=20\text{ V}$, $I_D=60\text{A}$, $R_G=4.7\Omega$, $V_{GS}=10\text{V}$ (see Figure 13)		19		ns ns
	Rise time			180		
$t_{d(off)}$ t_f	Off-voltage rise time	$V_{DD}=20\text{ V}$, $I_D=60\text{A}$, $R_G=4.7\Omega$, $V_{GS}=10\text{V}$ (see Figure 13)		90		ns ns
	Fall time			65		

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit		
I_{SD} I_{SDM}	Source-drain current				120	A		
	Source-drain current (pulsed)				480	A		
V_{SD}	Forward on voltage	$I_{SD}=120\text{A}$, $V_{GS}=0$			1.5	V		
	Reverse recovery time	$I_{SD}=120\text{A}$, $dI/dt = 100\text{A}/\mu\text{s}$, $V_{DD}=20\text{ V}$, $T_j=150^\circ\text{C}$ (see Figure 18)			67	ns		
	Reverse recovery charge				130	nC		
I_{RRM}	Reverse recovery current		4		A			

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Thermal impedance

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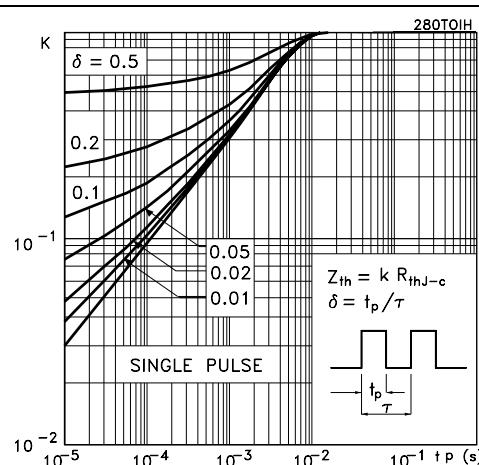
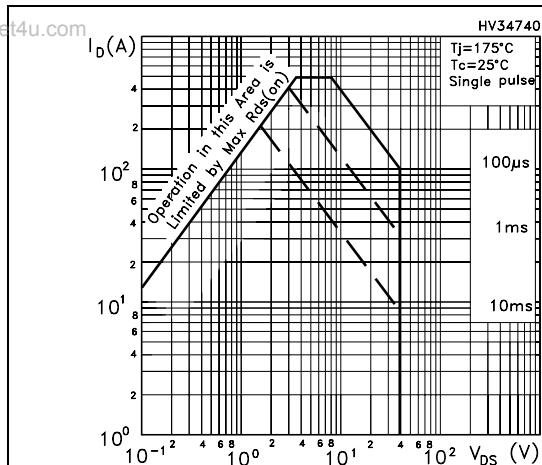


Figure 4. Output characteristics

Figure 5. Transfer characteristics

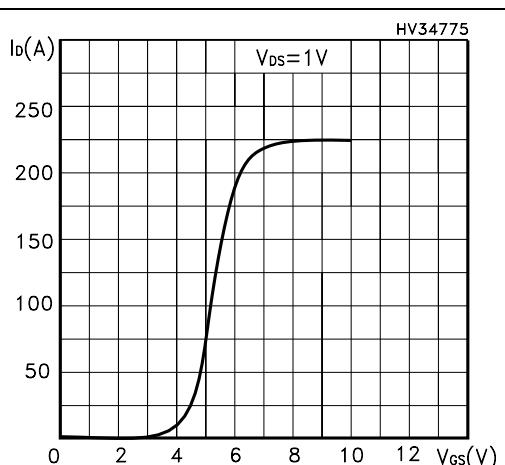
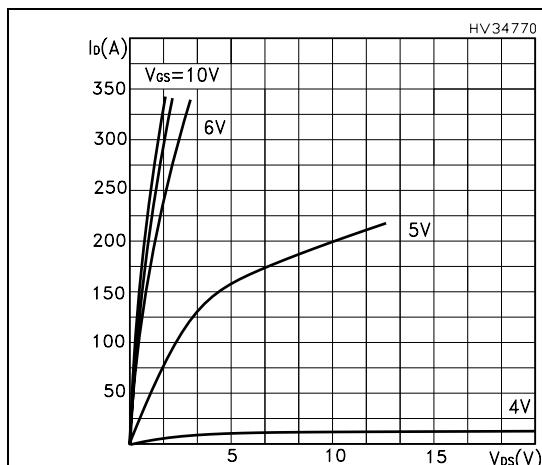
Figure 6. Normalized B_{VDSS} vs. temperature

Figure 7. Static drain-source on resistance

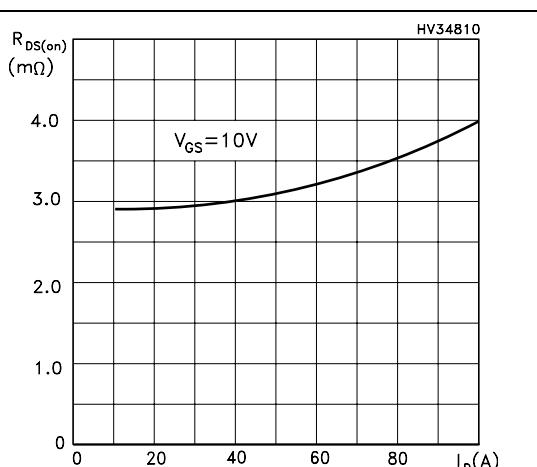
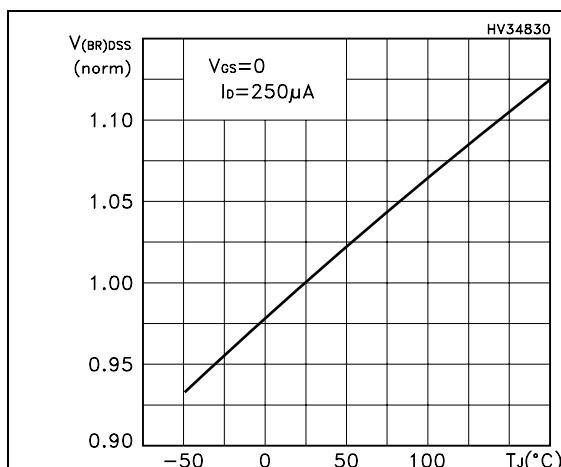
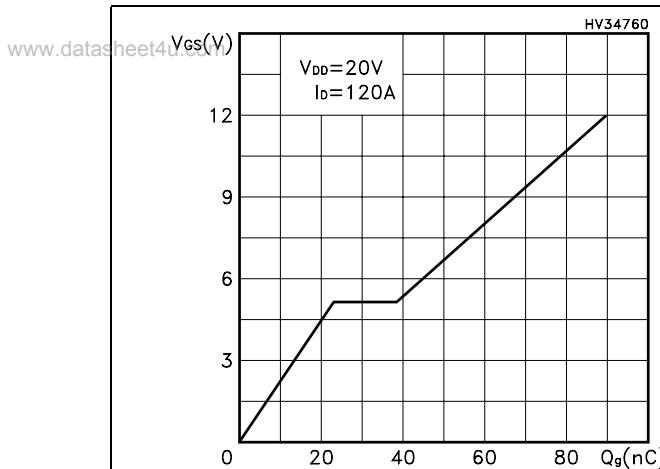
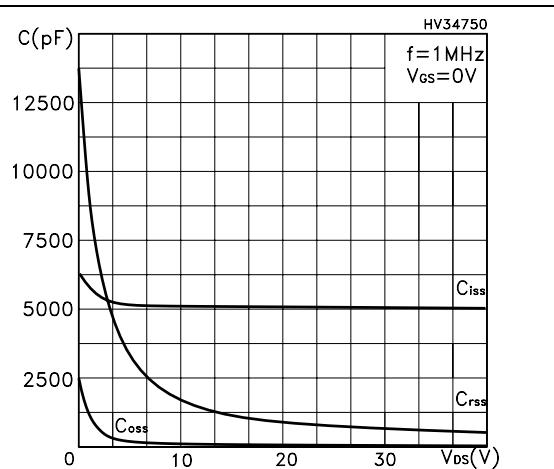
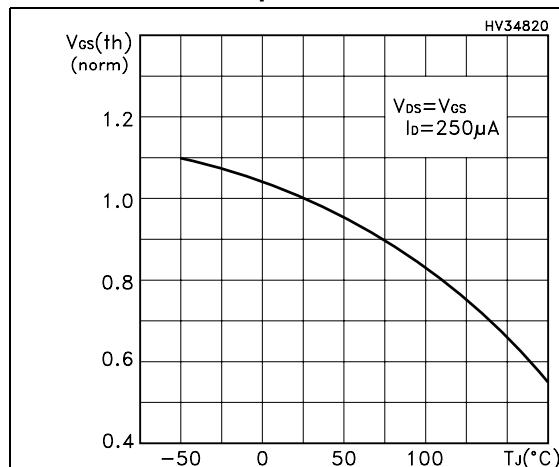
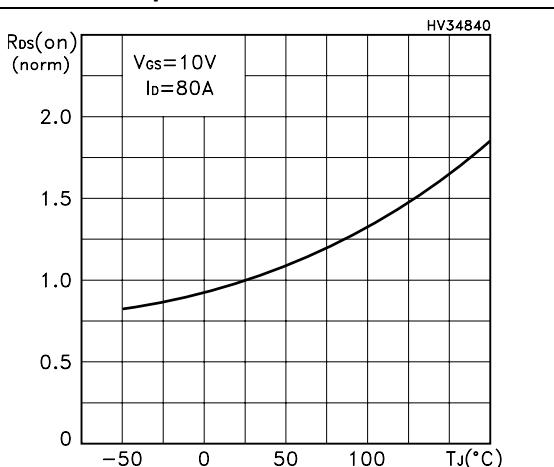
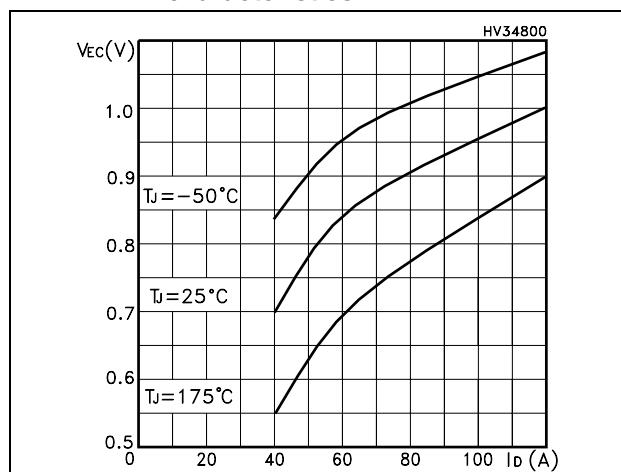


Figure 8. Gate charge vs. gate-source voltage**Figure 9. Capacitance variations****Figure 10. Normalized gate threshold voltage vs. temperature****Figure 11. Normalized on resistance vs. temperature****Figure 12. Source-drain diode forward characteristics**

3 Test circuit

Figure 13. Switching times test circuit for resistive load

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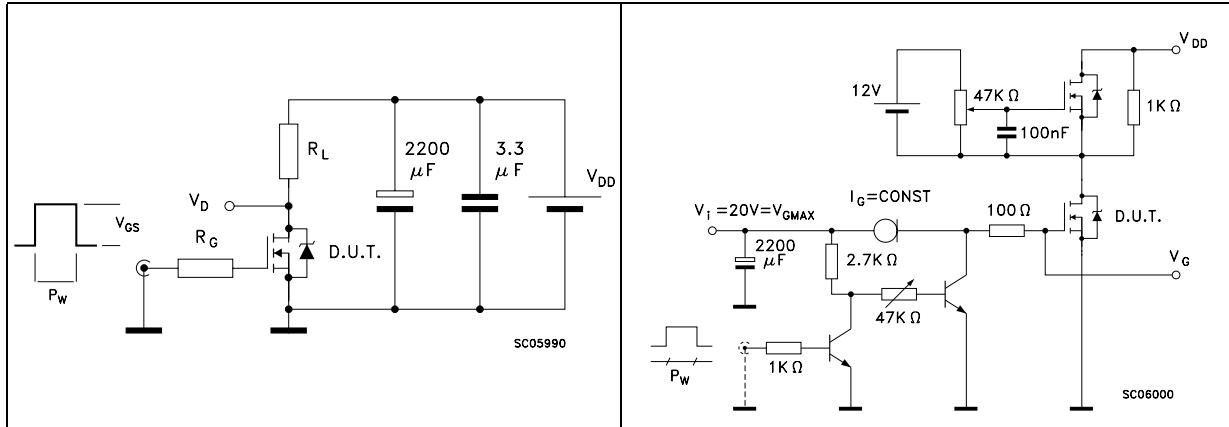


Figure 15. Test circuit for inductive load switching and diode recovery times

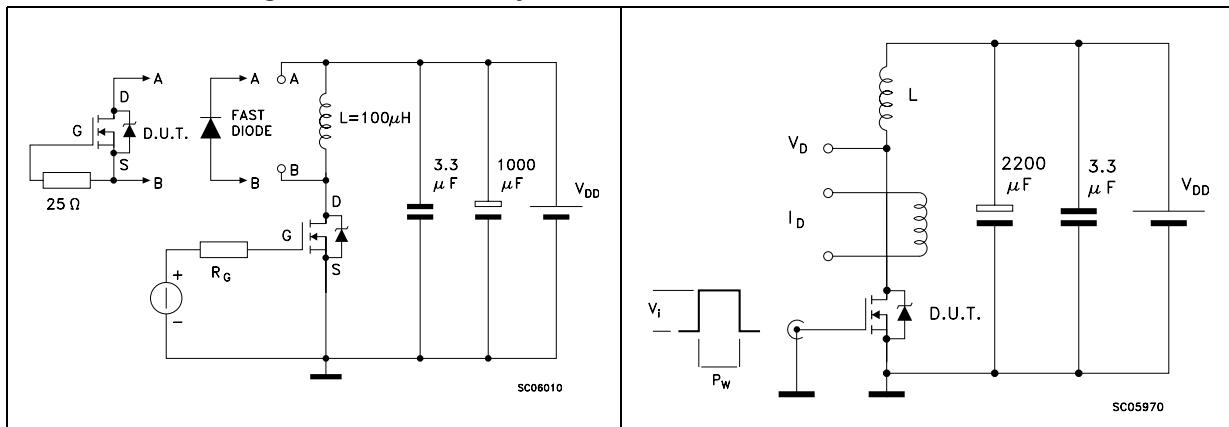


Figure 17. Unclamped inductive waveform

Figure 14. Gate charge test circuit

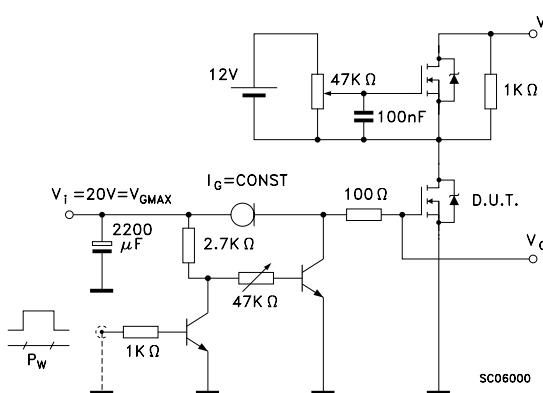


Figure 16. Unclamped Inductive load test circuit

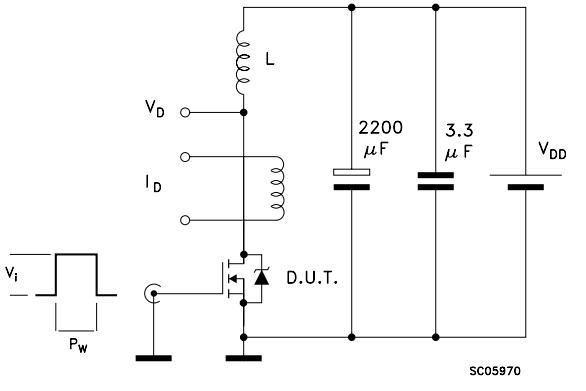
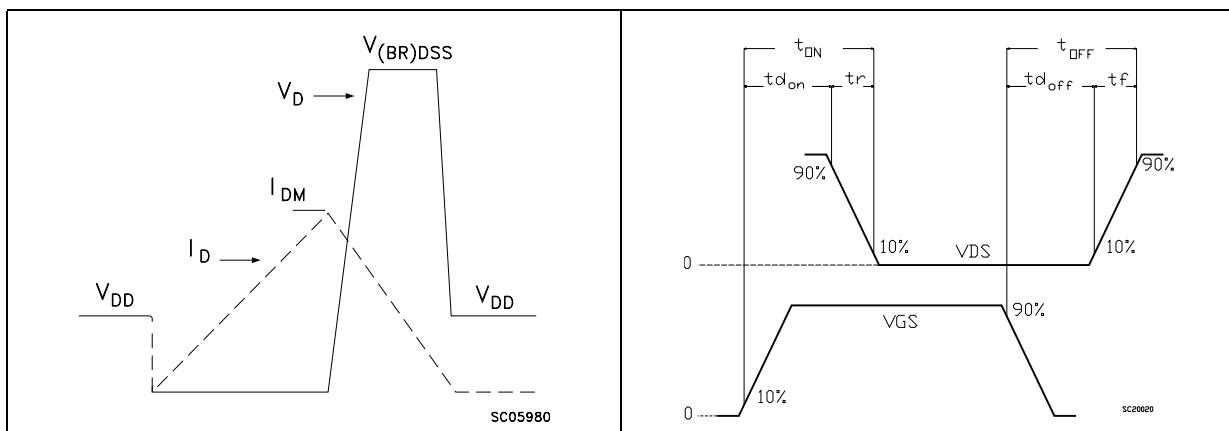


Figure 18. Switching time waveform



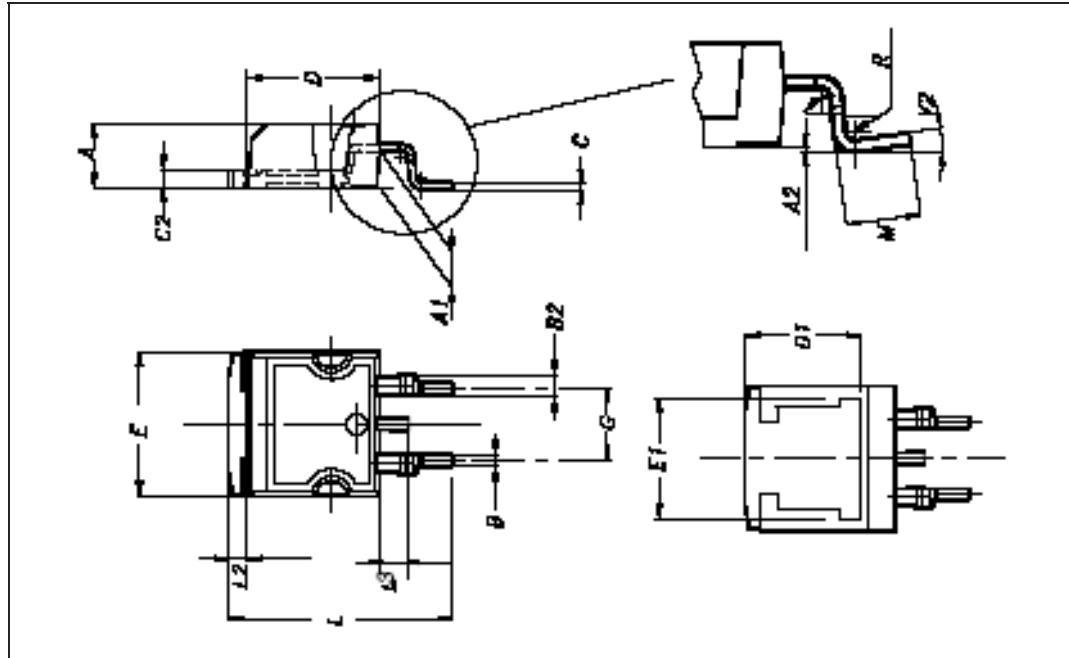
4 Package mechanical data

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In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

D²PAK mechanical data

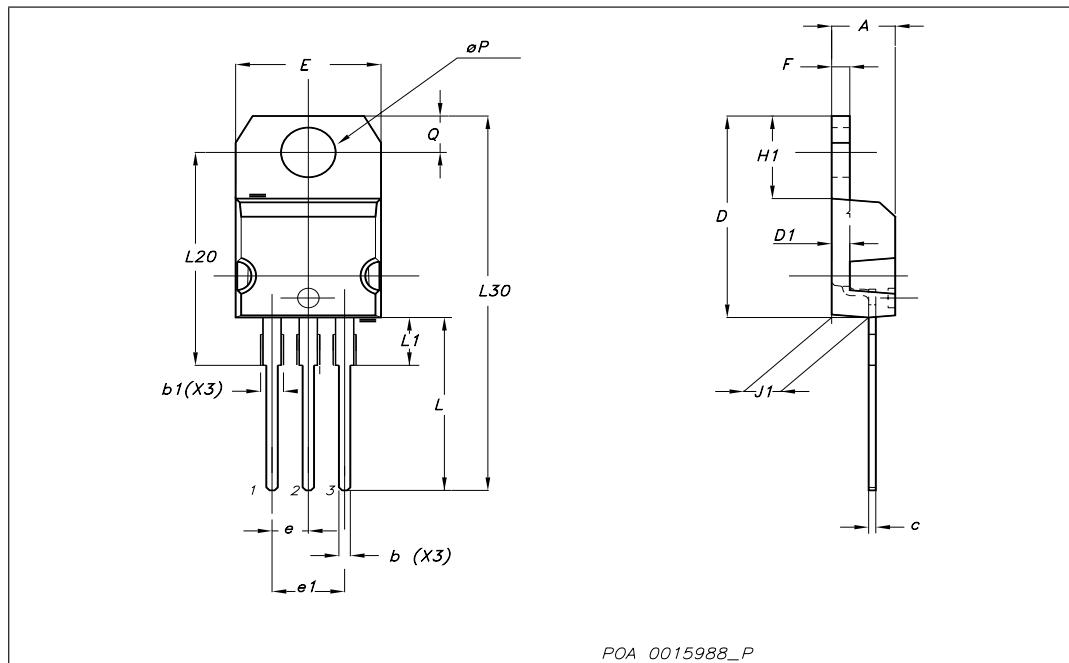
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	Min	Typ	Max	Min	Typ	Max
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		0.409
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.50		0.55
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



TO-220 mechanical data

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Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116

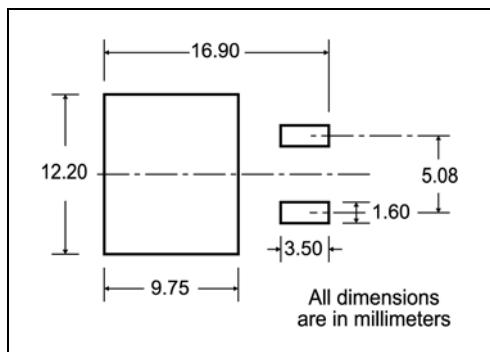


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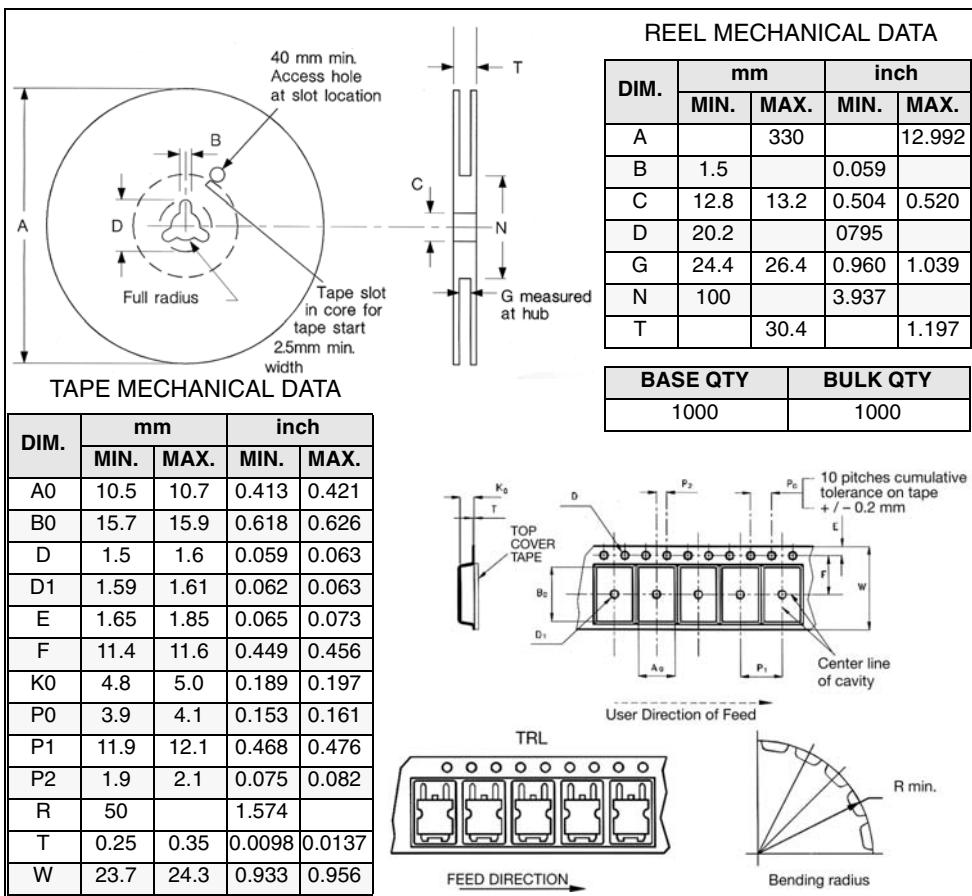
5 Packaging mechanical data

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D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 8. Document revision history

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Date	Revision	Changes
02-Mar-2007	1	First release
02-Oct-2007	2	Added TO-220 package

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